BAT74S

Dual Schottky barrier diode

22 November 2012

Product data sheet

1. Product profile

1.1 General description

Planar Schottky barrier dual diode with an integrated guard ring for stress protection. Two electrically isolated Schootky barrier diodes encapsulated in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

1.2 Features and benefits

- Low forward voltage
- Low capacitance
- AEC-Q101 qualified

1.3 Applications

- Ultra high-speed switching
- Line termination
- Voltage clamping
- Reverse polarity protection

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per diode	Per diode						
I _F	forward current			-	-	200	mA
V _R	reverse voltage			-	-	30	V
Per diode							,
V _F	forward voltage	I_F = 100 mA; pulsed; t_p = 300 μs; $δ$ = 0.02 ; T_{amb} = 25 °C		-	-	800	mV
I _R	reverse current	V_R = 25 V; pulsed; t_p = 300 µs; δ = 0.02 ; T_{amb} = 25 °C		-	-	2	μA





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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	A1	anode (diode 1)	654	K1 A2	
2	n.c.	not connected			
3	K2	cathode (diode 2)	TSSOP6 (SOT363)	- - - 	
4	A2	anode (diode 2)		∐1 ∐2 ∐3 aaa-005709	A1 K2 aaa-005709
5	n.c.	not connected			
6	K1	cathode (diode 1)			

3. Ordering information

Table 3. Ordering information

Type number		Package					
		Name	Description	Version			
	BAT74S	TSSOP6	plastic surface-mounted package; 6 leads	SOT363			

4. Marking

Table 4. Marking codes

Type number	Marking code [1]
BAT74S	74%

^{[1] % =} placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					,
V _R	reverse voltage		-	30	V
I _F	forward current		-	200	mA
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ s}; \ \delta \le 0.5$	-	300	mA
I _{FSM}	non-repetitive peak forward current	t_p < 10 ms; $T_{j(init)}$ = 25 °C	-	600	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	-	240	mW
Tj	junction temperature		-	125	°C

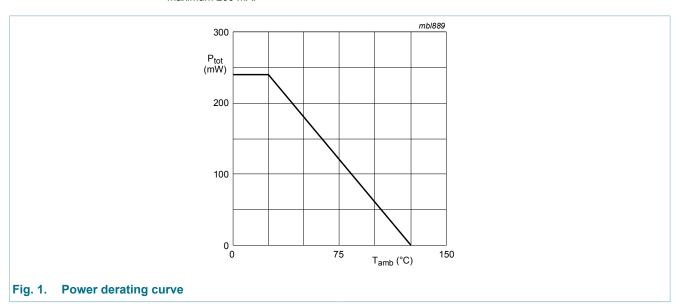
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Symbol	Parameter	Conditions		Min	Max	Unit
T _{amb}	ambient temperature			-55	125	°C
T _{stg}	storage temperature			-65	150	°C
Per device	Per device					
V _R	reverse voltage	series connection		-	60	V
				-	30	V
I _F	forward current		[1]	-	110	mA
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ s}; \ \delta \le 0.5$		-	200	mA

[1] If both diodes are in forward operation at the same moment, total device current is maximum 110 mA. If one diode is in reverse and the other in forward operation at the same moment, total device current is maximum 200 mA.



6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per diode							
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	416	K/W

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

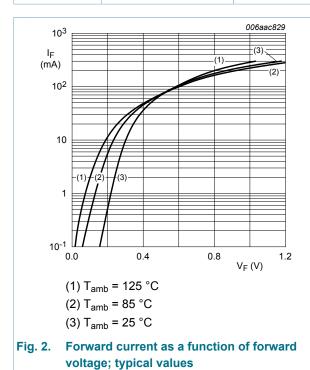
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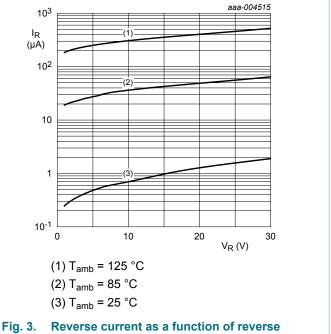
Dual Schottky barrier diode

7. Characteristics

Table 7 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
Per diode V _F	forward voltage	I_F = 0.1 mA; pulsed; t_p = 300 μs; $δ$ = 0.02; T_{amb} = 25 °C	-	-	240	mV
		I_F = 1 mA; pulsed; t_p = 300 µs; δ = 0.02; T_{amb} = 25 °C	-	-	320	mV
		I_F = 10 mA; pulsed; t_p = 300 μs; δ = 0.02 ; T_{amb} = 25 °C	d; t _p = 300 μs; 400 25 °C d; t _p = 300 μs; 500	mV		
		I_F = 30 mA; pulsed; t_p = 300 μs; δ = 0.02 ; T_{amb} = 25 °C		mV		
		I_F = 100 mA; pulsed; t_p = 300 μs; $δ$ = 0.02; T_{amb} = 25 °C	-		mV	
I _R	reverse current	V_R = 25 V; pulsed; t_p = 300 µs; δ = 0.02 ; T_{amb} = 25 °C	-	-	2	μA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz; T _{amb} = 25 °C	-	-	10	pF
t _{rr}	reverse recovery time	I_F = 10 mA; I_R = 10 mA; R_L = 100 Ω; $I_{R(meas)}$ = 1 mA; I_{amb} = 25 °C	-	-	5	ns

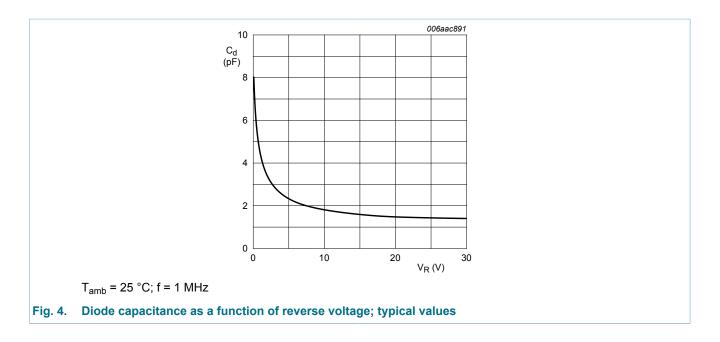




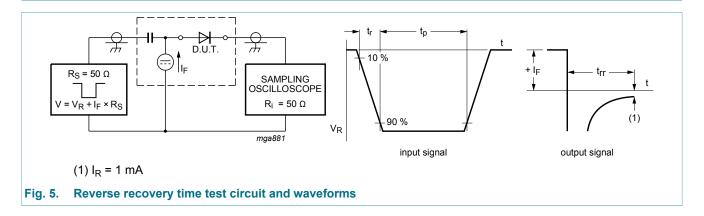
rig. 3. Reverse current as a function of reverse voltage; typical values

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8. Test information

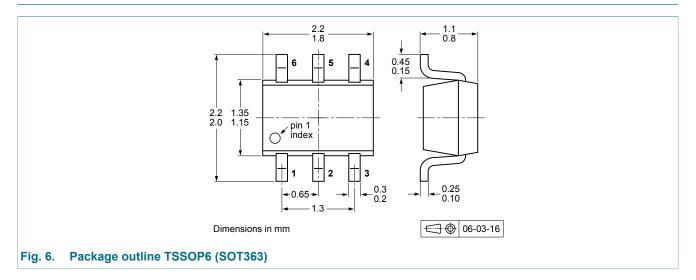


8.1 Quality information

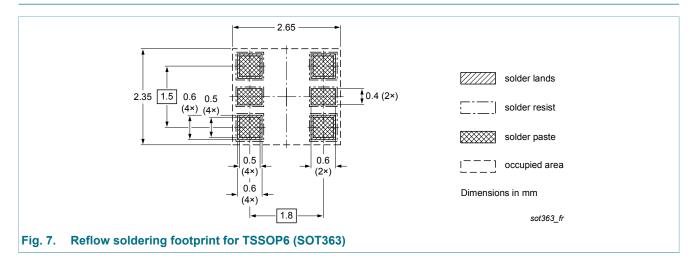
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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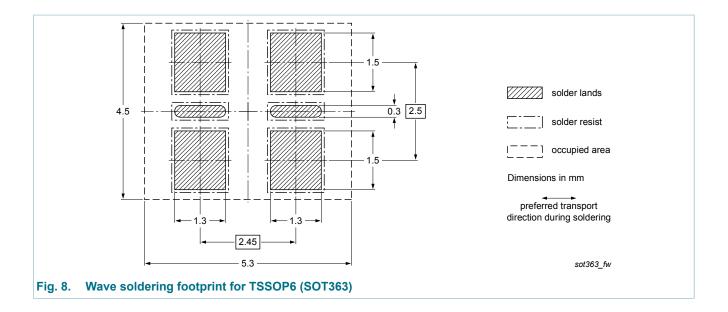
9. Package outline



10. Soldering



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11. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BAT74S v.5	20121122	Product data sheet	-	BAT74S v.4
Modifications:	 The format of this document has been redesigned to comply with the new identity guide of NXP Semiconductors. Legal texts have been adapted to the new company name where appropriate. Section 1 Product profile: updated Section 4 Marking: updated Table 5 Limiting values: changed Tamb minimum value to -55 °C according to AEC-Q10 Figure 2 and 3: updated Section 8 Test information: added Figure 6: superseded by minimized package outline drawing Section 10 Soldering: added Section 11 Legal information: updated 			
BAT74S v.4	20030411	Product specification	-	BAT74S v.3
BAT74S v.3	19980710	Product specification	-	BAT74S v.2
BAT74S v.2	19980206	Product specification	-	BAT74S v.1
BAT74S v.1	19971107	Product specification	-	-

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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